Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

2SJ148

High Speed Switching Applications Analog Switch Applications Interface Applications

- Excellent switching time: $t_{on} = 14 \text{ ns (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ mS (min)}$
- Low on resistance: RDS (ON) = 1.3 Ω (typ.)
- Enhancement-mode
- Complementary to 2SK982

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-60	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC	I _D	-200	mA	
	Pulse	I _{DP}	-800		
Drain power dissipation (Ta = 25°C)		P _D	400	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

1. SOURCE 2. DRAIN 3. GATE

JEDEC TO-92

JEITA SC-43

TOSHIBA 2-5F1H

Weight: 0.21 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of

high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

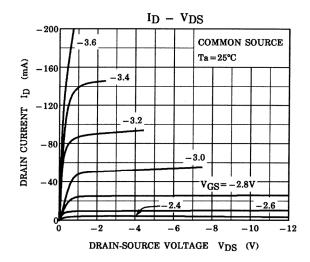


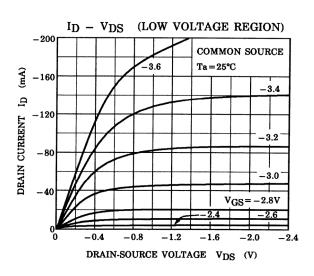
Electrical Characteristics (Ta = 25°C)

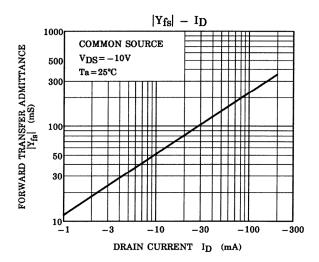
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curi	rent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±100	nA
Drain cut-off curre	ent	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0$	_	_	-10	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = -1 \text{ mA}, V_{GS} = 0$	-60	_	_	V
Gate threshold vo	ltage	V _{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-2	_	-3.5	V
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -50 \text{ mA}$	100	_	_	mS
Drain-source ON	resistance	R _{DS} (ON)	$I_D = -50 \text{ mA}, V_{GS} = -10 \text{ V}$		1.3	2.0	Ω
Drain-source ON	voltage	V _{DS (ON)}	$I_D = -50 \text{ mA}, V_{GS} = -10 \text{ V}$	_	-65	-100	mV
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz	_	73	85	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz	_	15	22	pF
Output capacitance		Coss	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz	_	48	60	pF
Switching time	Rise time	t _r	$I_{D} = -100 \text{mA}$ $-10V V_{IN} V_{IN} V_{DD} = -30V$ $V_{DD} = -30V$	_	8	_	ns
	Turn-on time	t _{on}		_	14	_	
	Fall time	t _f		_	35	_	
	Turn-off Time	t _{off}	$\begin{aligned} & V_{\text{IN}}\text{:}\ t_{\text{r}},\ t_{\text{f}} < 5\ \text{ns} \\ & \text{D.U.} \le 1\%\ (Z_{\text{out}} = 50\ \Omega) \end{aligned}$		100	_	

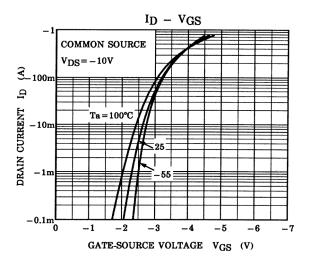
This transistor is the electrostatic sensitive device. Please handle with caution.

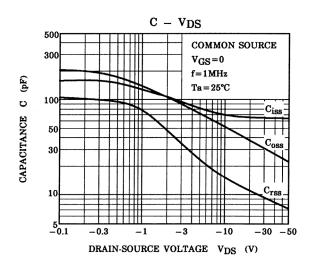
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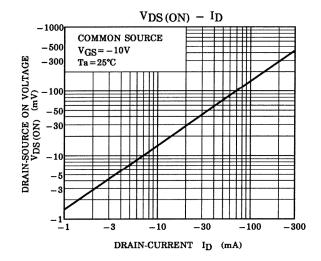


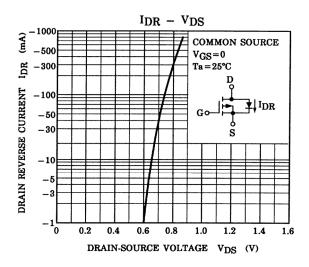


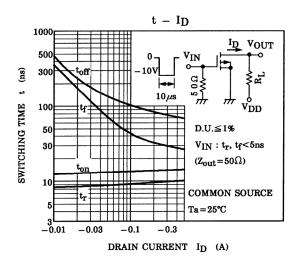


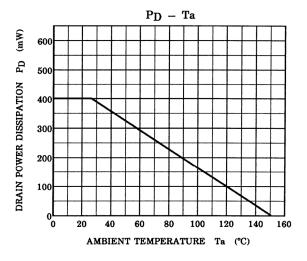












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20070701-EN GENERAL

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